

## ABSTRACT OF THE DISCLOSURE

A method for monitoring dynamic particle pollution in an etching chamber is provided. The method is described as follows. A bare wafer is positioned in an etching machine. Subsequently the bare wafer is transferred to a main etching chamber. Then, the plasma power source is turned on to perform an etching process on the photoresist. After that, the number of particles fallen on the bare wafer is counted to determine the polluted situation for the etching machine.